# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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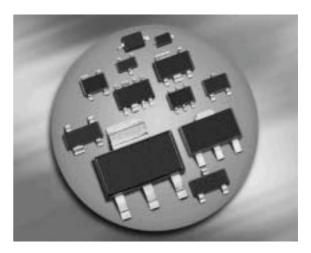




#### Silicon Switching Diode

- For high-speed switching applications
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101





#### BAL99



Туре	Package	Configuration	Marking
BAL99	SOT23	single	JFs

#### **Maximum Ratings** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V <sub>R</sub>	80	V	
Peak reverse voltage-	V <sub>RM</sub>	85		
Forward current	I <sub>F</sub>	250	mA	
Peak forward current	/ <sub>FM</sub>	-		
Surge forward current, $t = 1 \ \mu s$	IFS	4.5	A	
Total power dissipation	Ptot	370	mW	
$T_{\rm S} \le 54^{\circ}{\rm C}$				
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-65 150		

#### **Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>2)</sup>	R <sub>thJS</sub>	≤ 260	K/W

<sup>1</sup>Pb-containing package may be available upon special request

<sup>2</sup>For calculation of  $R_{\rm thJA}$  please refer to Application Note Thermal Resistance

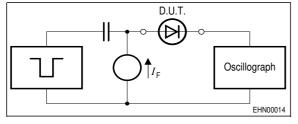


Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics		•	-		
Breakdown voltage	V <sub>(BR)</sub>	85	-	-	V
<i>I</i> (BR) = 100 μA					
Reverse current	l <sub>R</sub>				μA
<i>V</i> <sub>R</sub> = 70 V		-	-	1	
$V_{\rm R} = 25 \text{ V}, \ T_{\rm A} = 150 \ ^{\circ}{\rm C}$		-	-	30	
$V_{\rm R} = 70 \text{ V}, \ T_{\rm A} = 150 \ ^{\circ}{\rm C}$		-	-	50	
Forward voltage	VF				mV
$I_{\rm F} = 1  {\rm mA}$		-	-	715	
<i>I</i> <sub>F</sub> = 10 mA		-	-	855	
<i>I</i> <sub>F</sub> = 50 mA		-	-	1000	
<i>I</i> <sub>F</sub> = 150 mA		-	-	1250	
AC Characteristics					
Diode capacitance	CT	-	-	1.5	pF
$V_{R} = 0 V, f = 1 MHz$					
			-		

#### **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

$V_{\rm R} = 0  {\rm V},  f = 1  {\rm MHz}$					
Reverse recovery time	<i>t</i> rr	-	-	4	ns
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 10 mA, measured at $I_{\rm R}$ = 1mA ,					
$R_{\rm L} = 100 \ \Omega$					

#### Test circuit for reverse recovery time



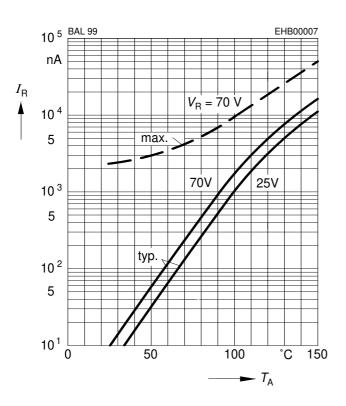
Puls generator:  $t_p = 100$ ns, D = 0.05,  $t_r = 0.6$ ns,  $R_i = 50\Omega$ Oscillograph: R = 50,  $t_r = 0.35$ ns

 $C \le 1 \text{pf}$ 



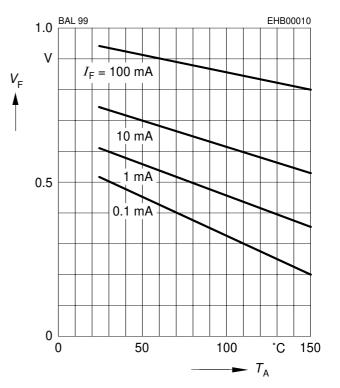
#### Reverse current $I_{R} = f(T_{A})$

 $V_{\rm R}$  = Parameter

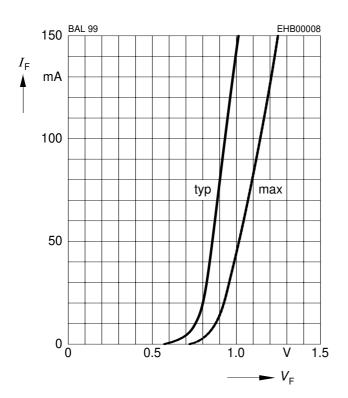


Forward Voltage  $V_{F} = f(T_{A})$ 

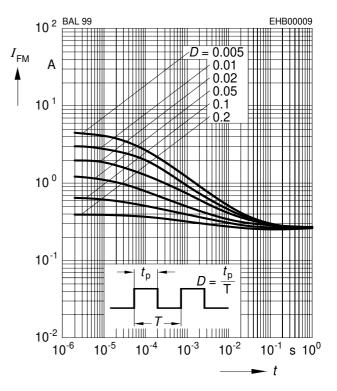
 $I_{\rm F}$  = Parameter



Forward current  $I_{\rm F} = f (V_{\rm F})$ 

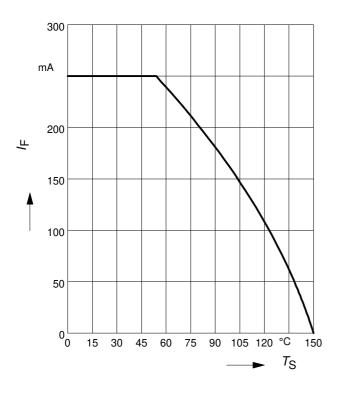


### **Peak forward current** $I_{FM} = f(t_p)$ $T_A = 25^{\circ}C$

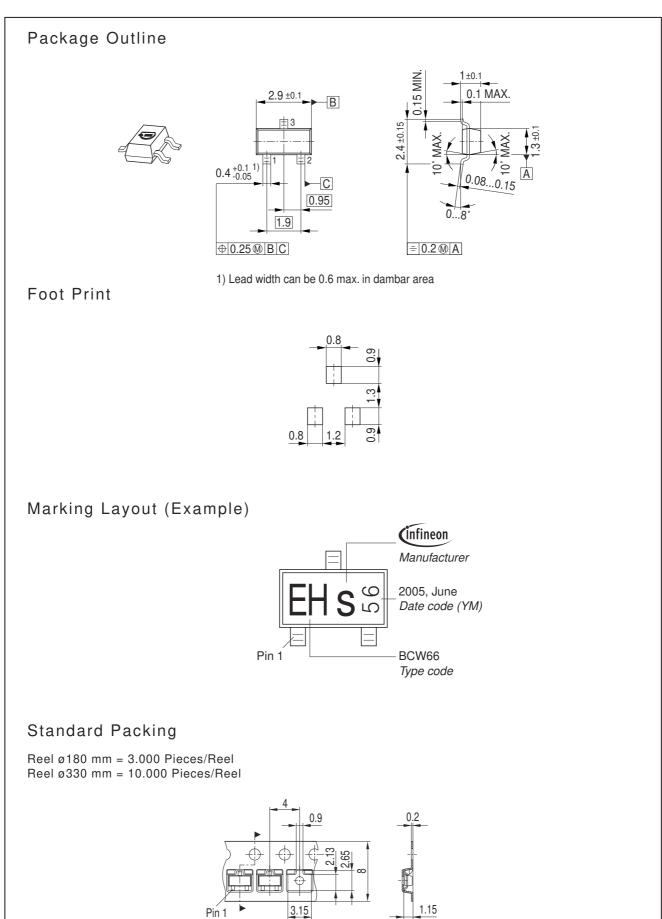




## Forward current $I_{\rm F} = f(T_{\rm S})$









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